



SLS SEMICONDUCTOR (SHENZHEN) CO.,LTD.

**SOT-23 封装半导体晶体管/SOT-23 Plastic-Encapsulate Transistors**

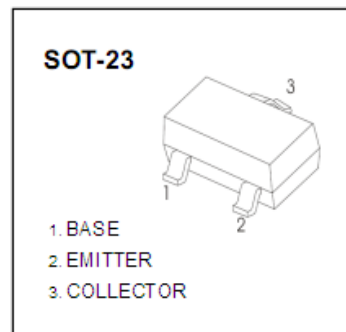
**BC817-16/BC817-25/BC817-40(NPN)**

**特点/Features :**

I<sub>c</sub>大, 电流增益大;

**用途/Applications :**

用于一般功率放大电路及开关, 与 BC807 互补。



**极限参数/Absolute maximum ratings(Ta=25°C)**

参数/Parameter	符号/ Symbol	数值/Value	单位/Unit
集电极-基极电压/Collector-Base Voltage	V <sub>CB0</sub>	50	V
集电极-发射极电压/Collector-Emitter Voltage	V <sub>CE0</sub>	45	V
发射极-基极电压/Emitter-Base Voltage	V <sub>EB0</sub>	5	V
集电极连续电流/Collector Current Continuous	I <sub>c</sub>	0.5	A
集电极耗散功率/Collector Power Dissipation	P <sub>c</sub>	0.3	W
结温/Junction Temperature	T <sub>j</sub>	150	°C
储存温度/Storage Temperature	T <sub>stg</sub>	-55~150	°C

**电性能参数/Electrical characteristics (Ta=25°C)**

参数	符号	测试条件	最小值	典型值	最大值	单位
集电极-基极击穿电压	V <sub>BR(CB0)</sub>	I <sub>c</sub> =10 μA, I <sub>E</sub> =0	50			V
集电极-发射极击穿电压	V <sub>BR(CE0)</sub>	I <sub>c</sub> =10mA, I <sub>B</sub> =0	45			V
发射极-基极击穿电压	V <sub>BR(EB0)</sub>	I <sub>E</sub> =1 μA, I <sub>c</sub> =0	5			V
集电极截止电流	I <sub>CB0</sub>	V <sub>CB</sub> =45V, I <sub>E</sub> =0			0.1	μA
发射极截止电流	I <sub>EB0</sub>	V <sub>EB</sub> =4V, I <sub>c</sub> =0			0.1	μA
直流电流增益	h <sub>FE(1)</sub>	V <sub>CE</sub> =1V, I <sub>c</sub> =100mA	100		600	
直流电流增益	h <sub>FE(2)</sub>	V <sub>CE</sub> =1V, I <sub>c</sub> =500mA	40			
集电极-发射极饱和压降	V <sub>CE(sat)</sub>	I <sub>c</sub> =500mA, I <sub>B</sub> =50mA			0.7	V
基极-发射极饱和压降	V <sub>BE(sat)</sub>	I <sub>c</sub> =500mA, I <sub>B</sub> =50mA			1.2	V
基极-发射极压降	V <sub>BE</sub>	V <sub>CE</sub> =1V, I <sub>c</sub> =500mA			1.2	V
特征频率	f <sub>T</sub>	V <sub>CE</sub> =5V, I <sub>c</sub> =10mA, f=100MHz	100			MHz
输出电容	C <sub>ob</sub>	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz		10		pF

**h<sub>FE</sub> 分档/Classification of h<sub>FE(1)</sub>**

档位/Rank	16	25	40
范围/Range	100~250	160~400	250~600
印章/Marking	6A	6B	6C



### 典型特性曲线图/Typical Characteristics

